

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete if Known

Application Number	10/760,028
Filing Date	January 16, 2004
First Named Inventor:	Robert Chau, et al.
Art Unit	2891
Examiner Name	Smith, Bradley
Attorney Docket No.:	42P17814

 Sheet **1** of **4**
U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner Signature	<i>JS/A</i>	Date Considered	7/25/06
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Substitute for Form 1449/PTO

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			US-				
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		Art Unit	2891	
		Examiner Name	Smith, Bradley	
Sheet	3	of	Attorney Docket No.:	42P17814

FOREIGN PATENT DOCUMENTS						
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		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				
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Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
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Examiner Signature	Date Considered		

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Sheet	4	of	4	Attorney Docket No.:	42P17814

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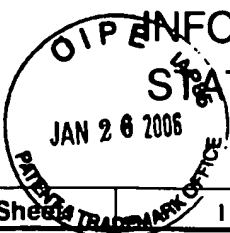
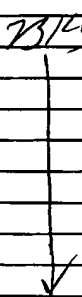
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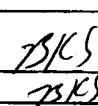
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		EP 1 202 335 A2	05/02/2002	IBM Corporation		
		EP 1 566 422 A2	08/24/2005	Samsung Electronics		

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		International Search Report PCT/US2005/010505			
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